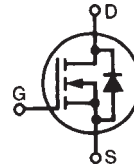


PolarHV™ HiPerFET Power MOSFET

IXFH 26N50P
IXFV 26N50P
IXFV 26N50PS

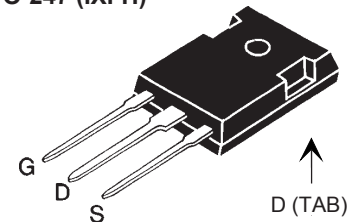
$V_{DSS} = 500 \text{ V}$
 $I_{D25} = 26 \text{ A}$
 $R_{DS(on)} \leq 230 \text{ m}\Omega$
 $t_{rr} \leq 200 \text{ ns}$

N-Channel Enhancement Mode
Avalanche Rated
Fast Intrinsic Diode

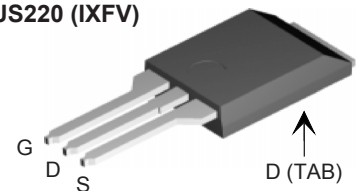


| Symbol | Test Conditions | Maximum Ratings | |
|------------|---|-----------------|------------------|
| | | | |
| V_{DSS} | $T_J = 25^\circ\text{C}$ to 150°C | 500 | V |
| V_{DGR} | $T_J = 25^\circ\text{C}$ to 150°C ; $R_{GS} = 1 \text{ M}\Omega$ | 500 | V |
| V_{GSS} | Continuous | ± 30 | V |
| V_{GSM} | Transient | ± 40 | V |
| I_{D25} | $T_C = 25^\circ\text{C}$ | 26 | A |
| I_{DM} | $T_C = 25^\circ\text{C}$, pulse width limited by T_{JM} | 78 | A |
| I_{AR} | $T_C = 25^\circ\text{C}$ | 26 | A |
| E_{AR} | $T_C = 25^\circ\text{C}$ | 40 | mJ |
| E_{AS} | $T_C = 25^\circ\text{C}$ | 1.0 | J |
| dv/dt | $I_S \leq I_{DM}$, $di/dt \leq 100 \text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ\text{C}$, $R_G = 4 \Omega$ | 10 | V/ns |
| P_D | $T_C = 25^\circ\text{C}$ | 400 | W |
| T_J | | -55 ... +150 | $^\circ\text{C}$ |
| T_{JM} | | 150 | $^\circ\text{C}$ |
| T_{stg} | | -55 ... +150 | $^\circ\text{C}$ |
| T_L | 1.6 mm (0.062 in.) from case for 10 s | 300 | $^\circ\text{C}$ |
| T_{SOLD} | Plastic body for 10 s | 260 | $^\circ\text{C}$ |
| M_d | Mounting torque (TO-247) | 1.13/10 | Nm/lb.in. |
| F_C | Mounting force (PLUS220) | 11..65/2.5..15 | N/lb |
| Weight | TO-247 | 6 | g |
| | PLUS220 & PLUS220SMD | 5 | g |

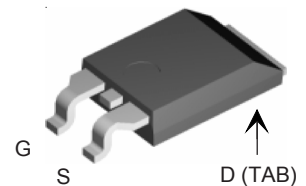
TO-247 (IXFH)



PLUS220 (IXFV)



PLUS220SMD (IXFV_S)



G = Gate D = Drain
S = Source TAB = Drain

| Symbol | Test Conditions ($T_J = 25^\circ\text{C}$, unless otherwise specified) | Characteristic Values | | |
|--------------|--|-----------------------|------|----------------------|
| | | Min. | Typ. | Max. |
| BV_{DSS} | $V_{GS} = 0 \text{ V}$, $I_D = 250 \mu\text{A}$ | 500 | | V |
| $V_{GS(th)}$ | $V_{DS} = V_{GS}$, $I_D = 4 \text{ mA}$ | 3.0 | | 5.5 V |
| I_{GSS} | $V_{GS} = \pm 30 \text{ V}_{DC}$, $V_{DS} = 0$ | | | $\pm 100 \text{ nA}$ |
| I_{DSS} | $V_{DS} = V_{DSS}$ $V_{GS} = 0 \text{ V}$ $T_J = 125^\circ\text{C}$ | | | 25 μA |
| | | | | 250 μA |
| $R_{DS(on)}$ | $V_{GS} = 10 \text{ V}$, $I_D = 0.5 I_{D25}$ Pulse test, $t \leq 300 \mu\text{s}$, duty cycle $d \leq 2 \%$ | | | 230 $\text{m}\Omega$ |

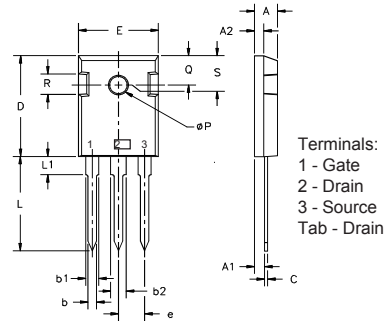
Features

- † International standard packages
- † Fast intrinsic diode
- † Unclamped Inductive Switching (UIS) rated
- † Low package inductance
 - easy to drive and to protect

Advantages

- † Easy to mount
- † Space savings
- † High power density

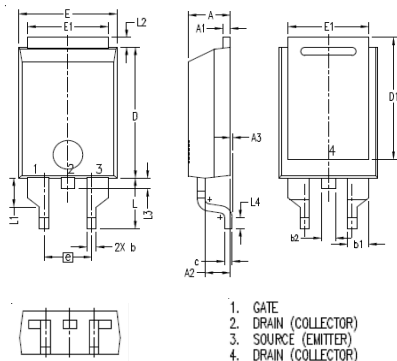
| Symbol | Test Conditions | Characteristic Values ($T_j = 25^\circ\text{C}$, unless otherwise specified) | | |
|--------------|---|---|------|--------------------------|
| | | Min. | Typ. | Max. |
| g_{fs} | $V_{DS} = 20\text{ V}$; $I_D = 0.5 I_{D25}$, pulse test | 16 | 26 | S |
| C_{iss} | $V_{GS} = 0\text{ V}$, $V_{DS} = 25\text{ V}$, $f = 1\text{ MHz}$ | | 3600 | pF |
| C_{oss} | | | 370 | pF |
| C_{rss} | | | 40 | pF |
| $t_{d(on)}$ | $V_{GS} = 10\text{ V}$, $V_{DS} = 0.5 I_{D25}$ $R_G = 4\ \Omega$ (External) | | 20 | ns |
| t_r | | | 25 | ns |
| $t_{d(off)}$ | | | 58 | ns |
| t_f | | | 20 | ns |
| $Q_{g(on)}$ | $V_{GS} = 10\text{ V}$, $V_{DS} = 0.5 V_{DSS}$, $I_D = 0.5 I_{D25}$ | | 60 | nC |
| Q_{gs} | | | 20 | nC |
| Q_{gd} | | | 25 | nC |
| R_{thJC} | (TO-247, PLUS220) | | | $0.31\ ^\circ\text{C/W}$ |
| R_{thCS} | | | 0.21 | $^\circ\text{C/W}$ |

TO-247 AD (IXFH) Outline


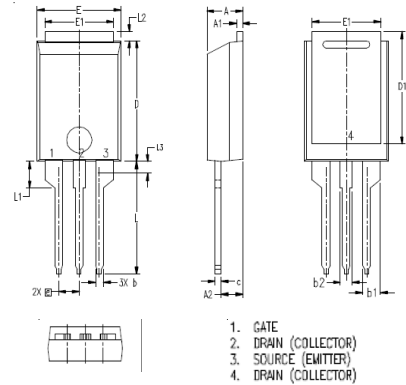
| Dim. | Millimeter | | Inches | |
|----------------|------------|-------|--------|-------|
| | Min. | Max. | Min. | Max. |
| A | 4.7 | 5.3 | .185 | .209 |
| A ₁ | 2.2 | 2.54 | .087 | .102 |
| A ₂ | 2.2 | 2.6 | .059 | .098 |
| b | 1.0 | 1.4 | .040 | .055 |
| b ₁ | 1.65 | 2.13 | .065 | .084 |
| b ₂ | 2.87 | 3.12 | .113 | .123 |
| C | .4 | .8 | .016 | .031 |
| D | 20.80 | 21.46 | .819 | .845 |
| E | 15.75 | 16.26 | .610 | .640 |
| e | 5.20 | 5.72 | 0.205 | 0.225 |
| L | 19.81 | 20.32 | .780 | .800 |
| L1 | | 4.50 | | .177 |
| ∅P | 3.55 | 3.65 | .140 | .144 |
| Q | 5.89 | 6.40 | 0.232 | 0.252 |
| R | 4.32 | 5.49 | .170 | .216 |
| S | 6.15 | BSC | .242 | BSC |

Source-Drain Diode

| Symbol | Test Conditions | Characteristic Values ($T_j = 25^\circ\text{C}$, unless otherwise specified) | | |
|----------|---|---|------|---------------|
| | | Min. | Typ. | Max. |
| I_S | $V_{GS} = 0\text{ V}$ | | | 26 A |
| I_{SM} | Repetitive | | | 104 A |
| V_{SD} | $I_F = I_S$, $V_{GS} = 0\text{ V}$, Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $d \leq 2\%$ | | | 1.5 V |
| t_{rr} | $I_F = 25\text{ A}$, $-di/dt = 100\text{ A}/\mu\text{s}$ $V_R = 100\text{ V}$, $V_{GS} = 0\text{ V}$ | | | 200 ns |
| Q_{RM} | | | 0.6 | μC |
| I_{RM} | | | 6 | A |

PLUS220SMD (IXFV_S) Outline


| SYM | INCHES | | MILLIMETER | |
|-----|---------|------|------------|-------|
| | MIN | MAX | MIN | MAX |
| A | .169 | .185 | 4.30 | 4.70 |
| A1 | .028 | .035 | 0.70 | 0.90 |
| A2 | .098 | .118 | 2.50 | 3.00 |
| A3 | .000 | .010 | 0.00 | 0.25 |
| b | .035 | .047 | 0.90 | 1.20 |
| b1 | .080 | .095 | 2.03 | 2.41 |
| b2 | .054 | .064 | 1.37 | 1.63 |
| c | .028 | .035 | 0.70 | 0.90 |
| D | .551 | .591 | 14.00 | 15.00 |
| D1 | .512 | .539 | 13.00 | 13.70 |
| E | .394 | .433 | 10.00 | 11.00 |
| E1 | .331 | .346 | 8.40 | 8.80 |
| e | .200BSC | | 5.08 | BSC |
| L | .209 | .228 | 5.30 | 5.80 |
| L1 | .118 | .138 | 3.00 | 3.50 |
| L2 | .035 | .051 | 0.90 | 1.30 |
| L3 | .047 | .059 | 1.20 | 1.50 |
| L4 | .039 | .059 | 1.00 | 1.50 |

PLUS220 (IXFV) Outline


| SYM | INCHES | | MILLIMETER | |
|-----|---------|------|------------|-------|
| | MIN | MAX | MIN | MAX |
| A | .169 | .185 | 4.30 | 4.70 |
| A1 | .028 | .035 | 0.70 | 0.90 |
| A2 | .098 | .118 | 2.50 | 3.00 |
| b | .035 | .047 | 0.90 | 1.20 |
| b1 | .080 | .095 | 2.03 | 2.41 |
| b2 | .054 | .064 | 1.37 | 1.63 |
| c | .028 | .035 | 0.70 | 0.90 |
| D | .551 | .591 | 14.00 | 15.00 |
| D1 | .512 | .539 | 13.00 | 13.70 |
| E | .394 | .433 | 10.00 | 11.00 |
| E1 | .331 | .346 | 8.40 | 8.80 |
| e | .100BSC | | 2.54 | BSC |
| L | .512 | .551 | 13.00 | 14.00 |
| L1 | .118 | .138 | 3.00 | 3.50 |
| L2 | .035 | .051 | 0.90 | 1.30 |
| L3 | .047 | .059 | 1.20 | 1.50 |

IXYS reserves the right to change limits, test conditions, and dimensions.

| | | | | | | | | |
|--|-----------|-----------|-----------|-----------|--------------|--------------|-------------|--------------|
| IXYS MOSFETs and IGBTs are covered by | 4,835,592 | 4,931,844 | 5,049,961 | 5,237,481 | 6,162,665 | 6,404,065 B1 | 6,683,344 | 6,727,585 |
| one or more of the following U.S. patents: | 4,850,072 | 5,017,508 | 5,063,307 | 5,381,025 | 6,259,123 B1 | 6,534,343 | 6,710,405B2 | 6,759,692 |
| | 4,881,106 | 5,034,796 | 5,187,117 | 5,486,715 | 6,306,728 B1 | 6,583,505 | 6,710,463 | 6,771,478 B2 |

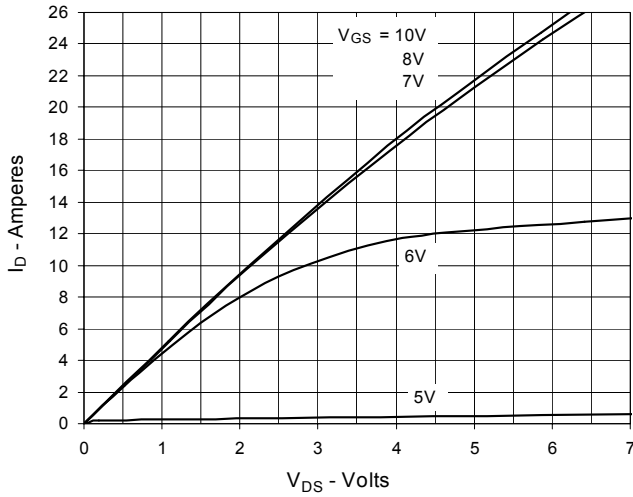
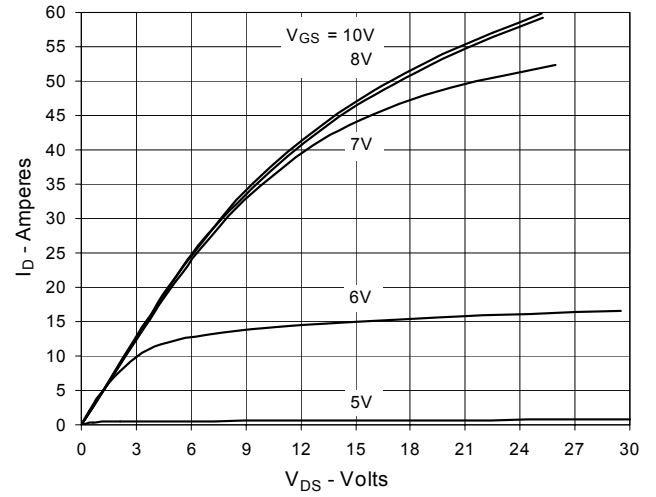
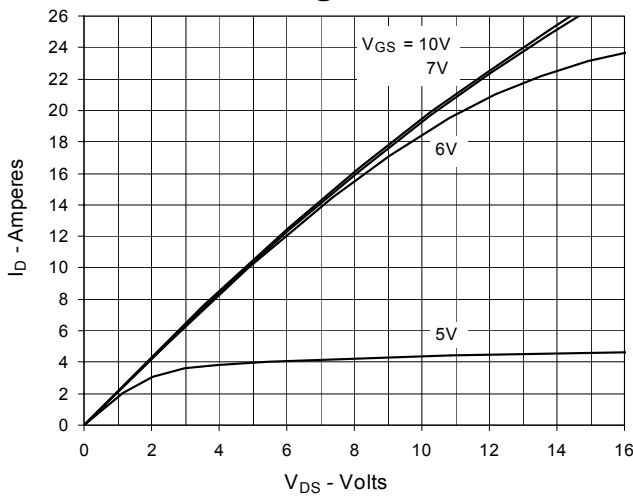
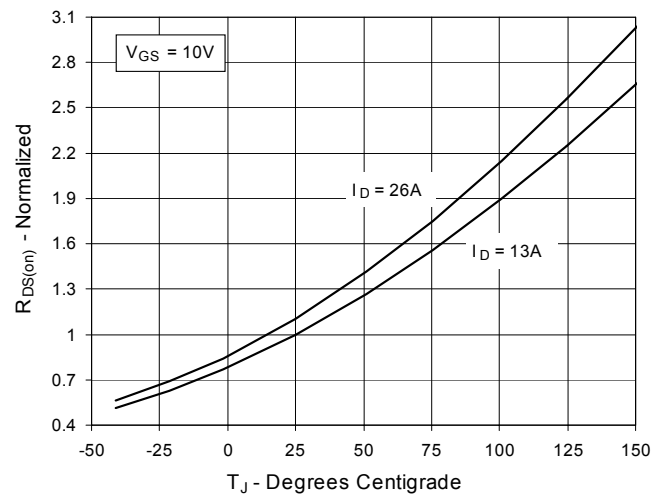
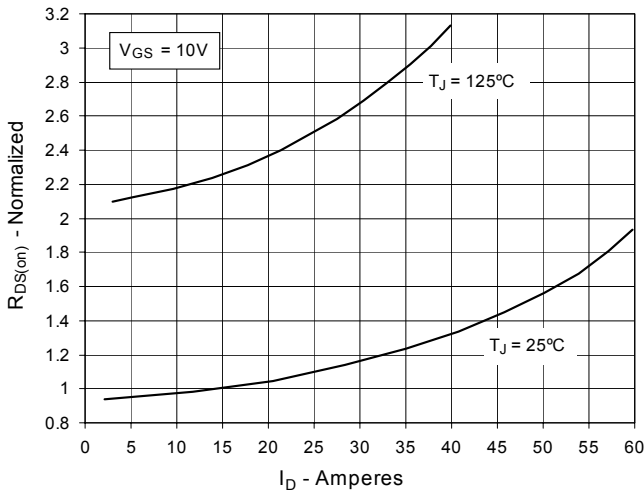
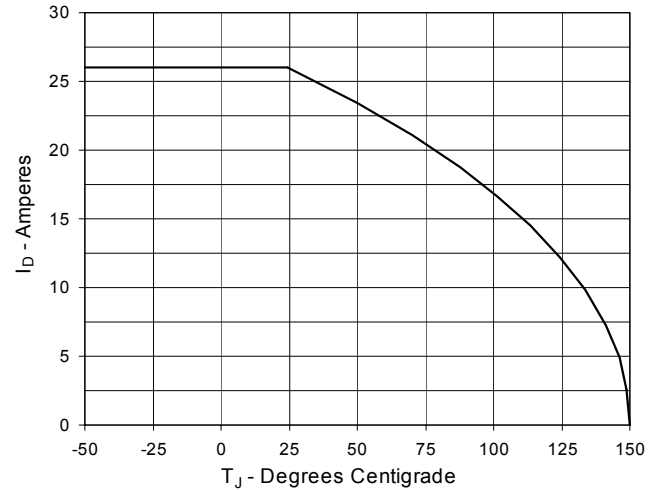
**Fig. 1. Output Characteristics
@ 25°C**

**Fig. 2. Extended Output Characteristics
@ 25°C**

**Fig. 3. Output Characteristics
@ 125°C**

**Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 13A$ Value
vs. Junction Temperature**

**Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 13A$ Value
vs. Drain Current**

**Fig. 6. Maximum Drain Current vs.
Case Temperature**


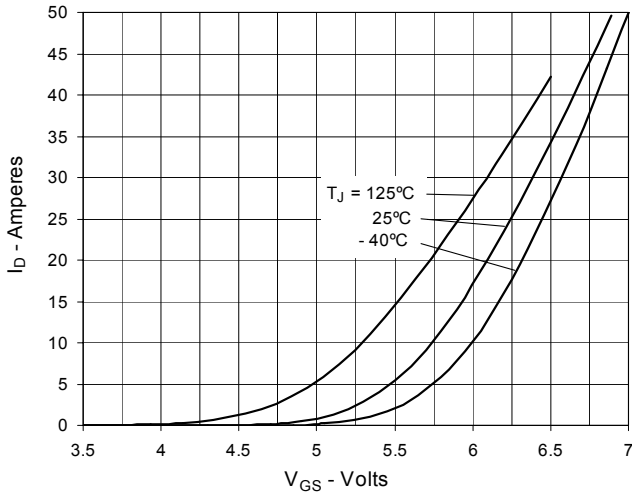
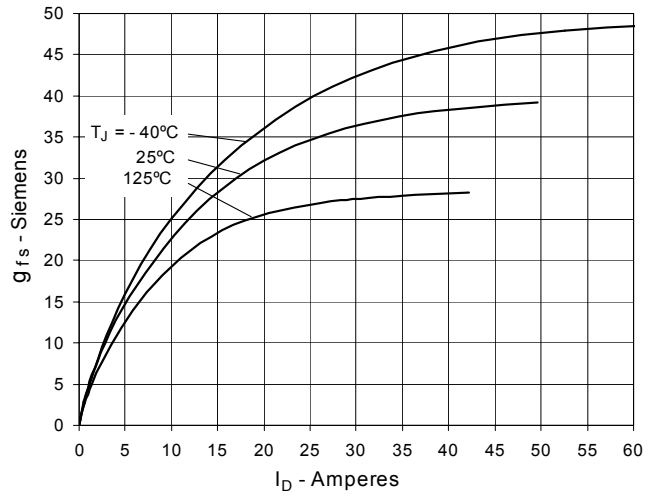
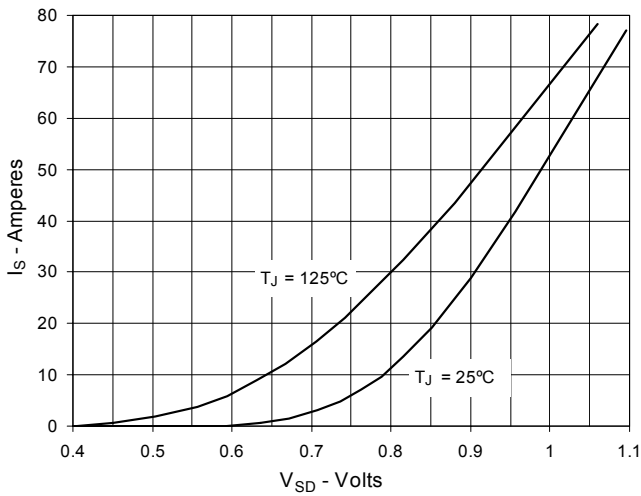
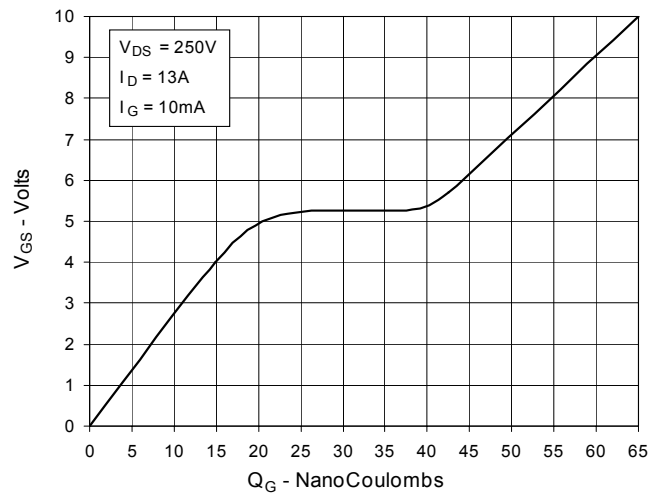
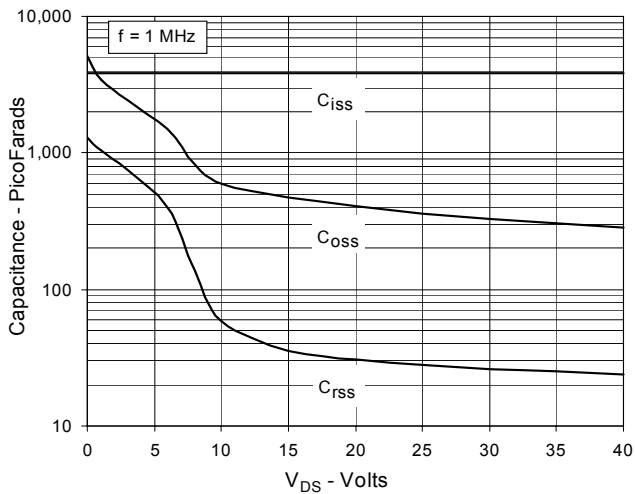
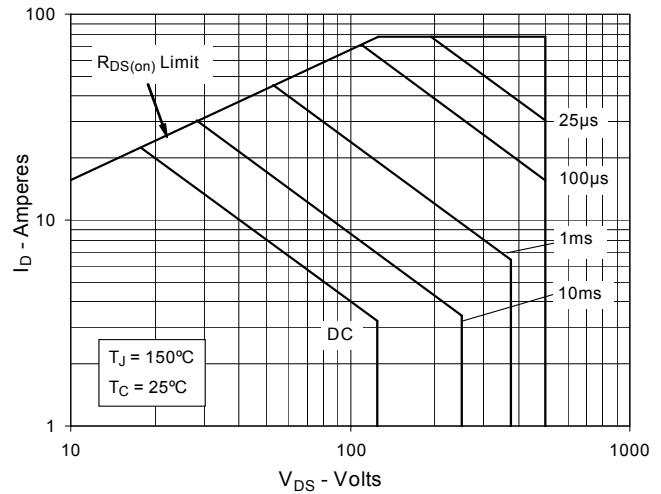
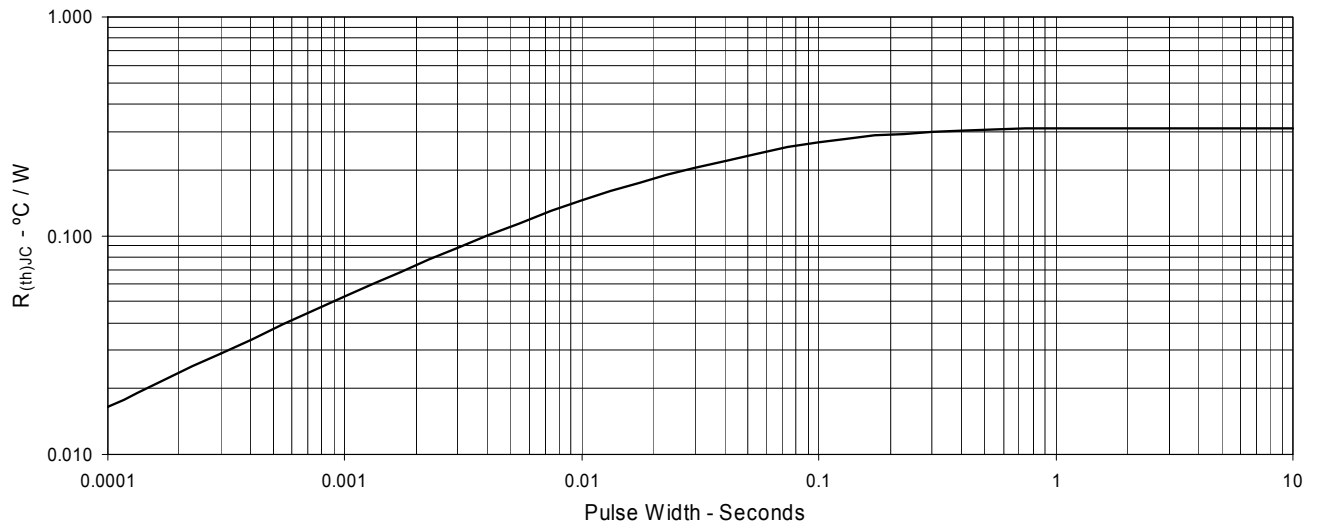
Fig. 7. Input Admittance

Fig. 8. Transconductance

Fig. 9. Forward Voltage Drop of Intrinsic Diode

Fig. 10. Gate Charge

Fig. 11. Capacitance

Fig. 12. Forward-Bias Safe Operating Area


Fig. 13. Maximum Transient Thermal Resistance



Disclaimer Notice - Information furnished is believed to be accurate and reliable. However, users should independently evaluate the suitability of and test each product selected for their own applications. Littelfuse products are not designed for, and may not be used in, all applications. Read complete Disclaimer Notice at www.littelfuse.com/disclaimer-electronics.